



DIM200PKM33-A000

IGBT Chopper Module

Preliminary Information

DS5598-1.1 April 2003

FEATURES

- 10 μ s Short Circuit Withstand
- High Thermal Cycling Capability
- Non Punch Through Silicon
- Isolated MMC Base with AlN Substrates

APPLICATIONS

- Choppers
- Traction Auxiliaries

The Powerline range of high power modules includes half bridge, chopper, dual, single and bi-directional switch configurations covering voltages from 600V to 3300V and currents up to 2400A.

The DIM200PKM33-A000 is a 3300V, n channel enhancement mode insulated gate bipolar transistor (IGBT) chopper module configured with the upper arm of the bridge controlled. The IGBT has a wide reverse bias safe operating area (RBSOA) plus full 10 μ s short circuit withstand. This device is optimised for applications requiring high thermal cycling capability.

The module incorporates an electrically isolated base plate and low inductance construction enabling circuit designers to optimise circuit layouts and utilise grounded heat sinks for safety.

ORDERING INFORMATION

Order As:

DIM200PKM33-A000

Note: When ordering, please use the whole part number.

KEY PARAMETERS

V_{CES}		3300V
$V_{CE(sat)}$ *	(typ)	3.2V
I_C	(max)	200A
$I_{C(PK)}$	(max)	400A

*(measured at the power busbars and not the auxiliary terminals)

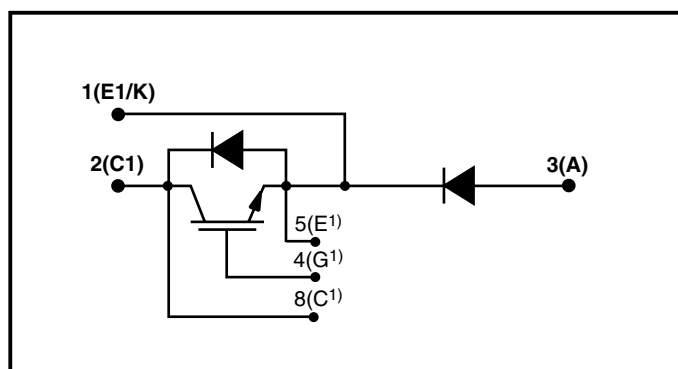


Fig. 1 Chopper circuit diagram - upper arm control

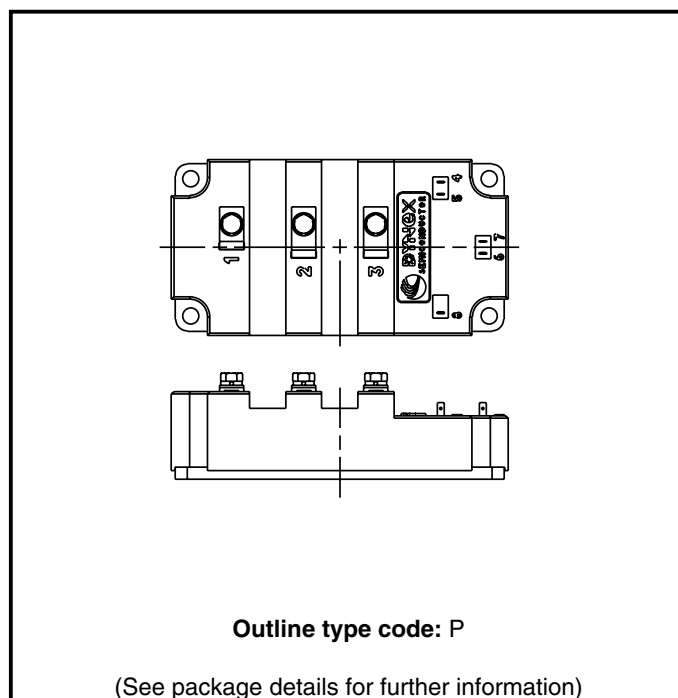


Fig. 2 Electrical connections - (not to scale)

Caution: This device is sensitive to electrostatic discharge. Users should follow ESD handling procedures.

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1/6

ABSOLUTE MAXIMUM RATINGS - IGBT ARM

Stresses above those listed under 'Absolute Maximum Ratings' may cause permanent damage to the device. In extreme conditions, as with all semiconductors, this may include potentially hazardous rupture of the package. Appropriate safety precautions should always be followed. Exposure to Absolute Maximum Ratings may affect device reliability.

$T_{case} = 25^{\circ}\text{C}$ unless stated otherwise

Symbol	Parameter	Test Conditions	Max.	Units
V_{CES}	Collector-emitter voltage	$V_{GE} = 0\text{V}$	3300	V
V_{GES}	Gate-emitter voltage	-	± 20	V
I_C	Continuous collector current	$T_{case} = 85^{\circ}\text{C}$	200	A
$I_{C(PK)}$	Peak collector current	1ms, $T_{case} = 115^{\circ}\text{C}$	400	A
P_{max}	Max. transistor power dissipation	$T_{case} = 25^{\circ}\text{C}$, $T_j = 150^{\circ}\text{C}$	2608	W
V_{isol}	Isolation voltage - per module	Commoned terminals to base plate. AC RMS, 1 min, 50Hz	6000	V
Q_{PD}	Partial discharge - per module	IEC1287. $V_1 = 2450\text{V}$, $V_2 = 1800\text{V}$, 50Hz RMS	10	pC

THERMAL AND MECHANICAL RATINGS

Internal insulation material: AlN
 Baseplate material: AlSiC
 Creepage distance: 33mm
 Clearance: 20mm
 CTI (Critical Tracking Index): 175

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
$R_{th(j-c)}$	Thermal resistance - transistor (IGBT arm)	Continuous dissipation - junction to case	-	-	48	$^{\circ}\text{C}/\text{kW}$
$R_{th(j-c)}$	Thermal resistance - diode (IGBT arm)	Continuous dissipation - junction to case	-	-	96	$^{\circ}\text{C}/\text{kW}$
	Thermal resistance - diode (diode arm)				96	$^{\circ}\text{C}/\text{kW}$
$R_{th(c-h)}$	Thermal resistance - case to heatsink (per module)	Mounting torque 5Nm (with mounting grease)	-	-	16	$^{\circ}\text{C}/\text{kW}$
T_j	Junction temperature	Transistor	-	-	150	$^{\circ}\text{C}$
		Diode	-	-	125	$^{\circ}\text{C}$
T_{stg}	Storage temperature range	-	-40	-	125	$^{\circ}\text{C}$
-	Screw torque	Mounting - M6	-	-	5	Nm
		Electrical connections - M5	-	-	4	Nm

ELECTRICAL CHARACTERISTICS

$T_{case} = 25^{\circ}\text{C}$ unless stated otherwise.

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
I_{CES}	Collector cut-off current	$V_{GE} = 0V, V_{CE} = V_{CES}$	-	-	1	mA
	(IGBT arm)	$V_{GE} = 0V, V_{CE} = V_{CES}, T_{case} = 125^{\circ}\text{C}$	-	-	15	mA
I_{GES}	Gate leakage current (IGBT arm)	$V_{GE} = \pm 20V, V_{CE} = 0V$	-	-	2	μA
$V_{GE(TH)}$	Gate threshold voltage (IGBT arm)	$I_C = 20\text{mA}, V_{GE} = V_{CE}$	4.5	5.5	6.5	V
$V_{CE(sat)}^{\dagger}$	Collector-emitter saturation voltage	$V_{GE} = 15V, I_C = 200A$	-	3.2	-	V
	(IGBT arm)	$V_{GE} = 15V, I_C = 200A, T_{case} = 125^{\circ}\text{C}$	-	4.0	-	V
I_F	Diode forward current (IGBT arm)	DC	-	200	-	A
	Diode forward current (diode arm)	DC	-	200	-	A
I_{FM}	Diode maximum forward current	$t_p = 1\text{ms}$	-	400	-	A
	(IGBT arm)					
I_{FM}	Diode maximum forward current	$t_p = 1\text{ms}$	-	400	-	A
	(diode arm)					
V_F^{\dagger}	Diode forward voltage	$I_F = 200A$ (IGBT arm)	-	2.5	-	V
		$I_F = 200A$ (Diode arm)	-	2.5	-	V
		$I_F = 200A, T_{case} = 125^{\circ}\text{C}$ (IGBT arm)	-	2.5	-	V
		$I_F = 200A, T_{case} = 125^{\circ}\text{C}$ (diode arm)	-	2.5	-	V
C_{ies}	Input capacitance (IGBT arm)	$V_{CE} = 25V, V_{GE} = 0V, f = 1\text{MHz}$	-	45	-	nF
C_{res}	Reverse transfer capacitance (IGBT arm)	$V_{CE} = 25V, V_{GE} = 0V, f = 1\text{MHz}$	-	2.5	-	nF
L_M	Module inductance - per switch	-	-	30	-	nH
R_{INT}	Internal transistor resistance (IGBT arm)	-	-	0.54	-	m Ω
SC_{Data}	Short circuit. I_{SC}	$T_j = 125^{\circ}\text{C}, V_{CC} = 2500V,$	I_1	1300		A
		$t_p \leq 10\mu\text{s}, V_{CE(max)} = V_{CES} - L^* \cdot di/dt$ IEC 60747-9	I_2	1100		A

Note:

\dagger Measured at the power busbars and not the auxiliary terminals)

L^* is the circuit inductance + L_M

Caution: This device is sensitive to electrostatic discharge. Users should follow ESD handling procedures.

3/6

DIM200PKM33-A000**ELECTRICAL CHARACTERISTICS - IGBT ARM****T_{case} = 25°C unless stated otherwise**

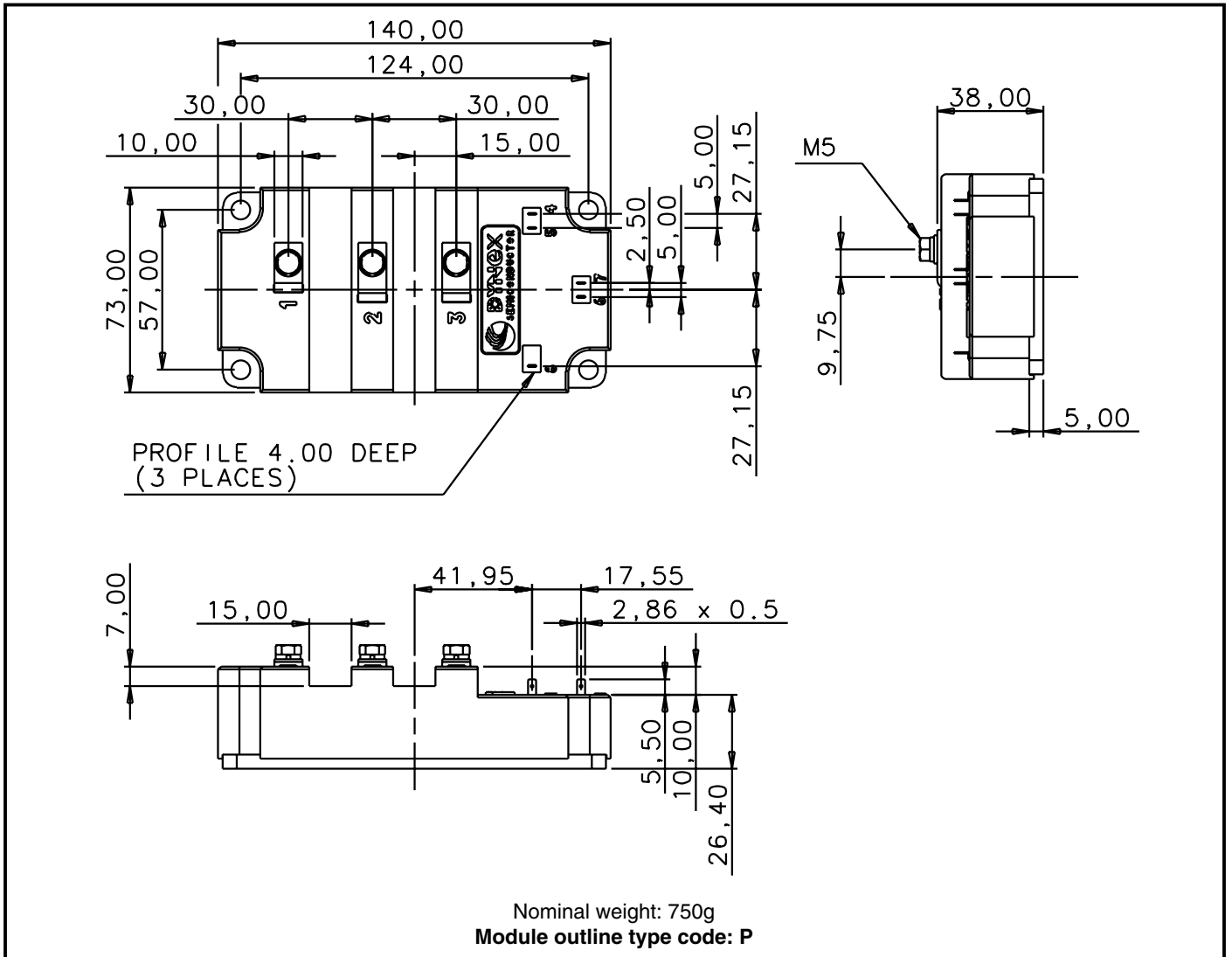
Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
t _{d(off)}	Turn-off delay time	$I_C = 200A$ $V_{GE} = \pm 15V$ $V_{CE} = 1800V$ $R_{G(ON)} = R_{G(OFF)} = 10\Omega$ $C_{ge} = 33nF$ $L \sim 100nH$	-	1300	-	ns
t _f	Fall time		-	200	-	ns
E _{OFF}	Turn-off energy loss		-	170	-	mJ
t _{d(on)}	Turn-on delay time		-	640	-	ns
t _r	Rise time		-	250	-	ns
E _{ON}	Turn-on energy loss		-	290	-	mJ
Q _g	Gate charge		-	6	-	μC
Q _{rr}	Diode reverse recovery charge	$I_F = 200A, V_R = 1800V,$ $dI_F/dt = 1100A/\mu s$	-	115	-	μC
I _{rr}	Diode reverse current		-	165	-	A
E _{REC}	Diode reverse recovery energy		-	130	-	mJ

T_{case} = 125°C unless stated otherwise

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
t _{d(off)}	Turn-off delay time	$I_C = 200A$ $V_{GE} = \pm 15V$ $V_{CE} = 1800V$ $R_{G(ON)} = R_{G(OFF)} = 10\Omega$ $C_{ge} = 33nF$ $L \sim 100nH$	-	1600	-	ns
t _f	Fall time		-	250	-	ns
E _{OFF}	Turn-off energy loss		-	240	-	mJ
t _{d(on)}	Turn-on delay time		-	640	-	ns
t _r	Rise time		-	300	-	ns
E _{ON}	Turn-on energy loss		-	420	-	mJ
Q _{rr}	Diode reverse recovery charge		$I_F = 200A, V_R = 1800V,$ $dI_F/dt = 1000A/\mu s$	-	190	-
I _{rr}	Diode reverse current	-		185	-	A
E _{REC}	Diode reverse recovery energy	-		220	-	mJ

PACKAGE DETAILS

For further package information, please visit our website or contact Customer Services. All dimensions in mm, unless stated otherwise. DO NOT SCALE.



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POWER ASSEMBLY CAPABILITY

The Power Assembly group was set up to provide a support service for those customers requiring more than the basic semiconductor, and has developed a flexible range of heatsink and clamping systems in line with advances in device voltages and current capability of our semiconductors.

We offer an extensive range of air and liquid cooled assemblies covering the full range of circuit designs in general use today. The Assembly group offers high quality engineering support dedicated to designing new units to satisfy the growing needs of our customers.

Using the latest CAD methods our team of design and applications engineers aim to provide the Power Assembly Complete Solution (PACs).

HEATSINKS

The Power Assembly group has its own proprietary range of extruded aluminium heatsinks which have been designed to optimise the performance of Dynex semiconductors. Data with respect to air natural, forced air and liquid cooling (with flow rates) is available on request.

For further information on device clamps, heatsinks and assemblies, please contact your nearest sales representative or Customer Services.



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Advance Information: The product design is complete and final characterisation for volume production is well in hand.

No Annotation: The product parameters are fixed and the product is available to datasheet specification.

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